



InGaN/GaN Blue Chip (13mil)

Device No. : MOC13A465
MOC13A467

Scope

- The specification applies to InGaN LED chips

Structure

- InGaN/GaN Blue Chip
- Bond pad P(anode) pad : Au
N(cathode) pad : Au

Size

- Chip size : 295 μ m \times 340 μ m
- Chip Thickness : 110 μ m
- Measurement tolerance \pm 10 μ m
- Pattern drawing : per fig.1

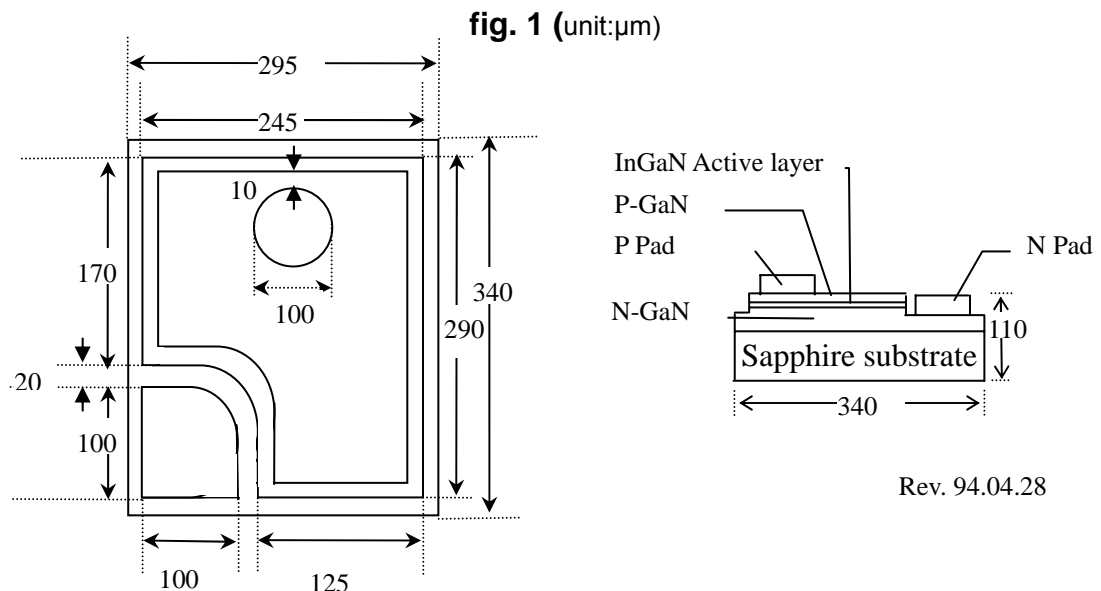
Electro-Optical Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	2.9	3.4	3.8	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	10	--	--	V
Reverse Current	I_R	$V_R = 5\text{V}$	--	--	2	μA
Luminous Intensity	I_V	$I_F = 20\text{mA}$				mcd
Wavelength	λ_D	$I_F = 20\text{mA}$	465	--	470	nm

The measurements base on chip on wafer form.

Rank I: 60~70, Rank J: 70~80, Rank K:80~90,

Rank L: 90~100, Rank M: 100~120, Rank O: 120~140, Rank Q: 140 \uparrow



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